ELSEVIER

Journal of Crystal Growth 170 (1997) 822–833

JOURNAL OF CRYSTAL GROWTH

# Author index

Adam, D., see Ortion, J.M. 170 (1997) 674
Adler, F., see Geiger, M. 170 (1997) 558
Ahern, B.S., see Weyburne, D.W. 170 (1997) 77
Aiga, M., see Takiguchi, T. 170 (1997) 705
Aina, L., see Thompson, A.G. 170 (1997) 92
Alexander, W.B., see Wickenden, A.E. 170 (1997) 367
Ambacher, O., see Fischer, R.A. 170 (1997) 139
Ambacher, O., R. Dimitrov, D. Lentz, T. Metzger, W. Rieger and M. Stutzmann, Growth of GaN/AlN and AlGaN by MOCVD using triethylgallium and tritertiarybutylaluminium 170 (1997) 335
Anand, S., see Carlsson, N. 170 (1997) 127
Anders, M.J., see Hageman, P.R. 170 (1997) 270
Anders, M.J., see Bastos, P.L. 170 (1997) 710
Ando, H., Recent progress in multi-wafer CBE systems 170 (1997) 16
Ando, H., see Ando, S. 170 (1997) 719
Ando, S., N. Kobayashi, H. Ando and Y. Horikoshi, Hexagonal facet laser with optical waveguides grown by flow-rate modulation epitaxy 170 (1997) 719
Aoki, M., see Suzuki, M. 170 (1997) 661
Aoki, S., see Funato, M. 170 (1997) 276
Aoyagi, Y., see Tanaka, S. 170 (1997) 329
Arai, T., J. Hidaka, H. Tokunaga and K. Matsumoto, Highly uniform growth in a low-pressure MOVPE multiple wafer system 170 (1997) 88
Arakawa, Y., see Kitamura, M. 170 (1997) 563
Arès, R., S.P. Watkins and C.A. Tran, Breakdown of self-limiting behaviour in InAs/GaAs heterostructures grown by atomic layer epitaxy 170 (1997) 574
Arès, R., see Watkins, S.P. 170 (1997) 788
Armour, E., see Thompson, A.G. 170 (1997) 92
Ayers, J.E., see Bao, K.X. 170 (1997) 497

Baker, J.E., see Islam, M.R. 170 (1997) 413
Bao, K.X., R. Mo, X.G. Zhang, S. Kalisetty, M. Gokhale, J. Robinson, G. Zhao, J.E. Ayers and F.C. Jain, Compositional control of $Cd_xZn_{1-x}Se$ grown by photoassisted organometallic vapor phase epitaxy 170 (1997) 497
Basilavecchia, M., see Gurskii, A.L. 170 (1997) 533
Baskar, K., see Soga, T. 170 (1997) 447
Bastos, P.L., M.J. Anders, M.M.G. Bongers, P.R. Hageman and L.J. Giling, Temperature dependence on the emerging crystal habit of GaInP deposited on nonplanar {001}GaAs substrates 170 (1997) 710
Bauknecht, A., see Geiger, M. 170 (1997) 558
Baumeister, H., see Keidler, M. 170 (1997) 161
Beaumont, B., M. Vaille, T. Boufaden, B. el Jani and P. Gibart, High quality GaN grown by MOVPE 170 (1997) 316
Beccard, R., G. Lengeling, D. Schmitz, Y. Gigase and H. Jürgensen, Replacement of hydrides by TBAs and TBP for the growth of various III–V materials in production scale MOVPE reactors 170 (1997) 97
Becht, M., F. Wang, J.G. Wen and T. Morishita, Evolution of the microstructure of oxide thin films 170 (1997) 799
Beckham, C., see Thompson, A.G. 170 (1997) 92
Behet, M., see Tümmler, J. 170 (1997) 772
Behet, M., see von Eichel-Streiber, C. 170 (1997) 783
Behres, A., H. Werner, A. Kohl and K. Heime, InP growth on ion-implanted InP substrate: a new method to achieve selective area MOVPE 170 (1997) 655
Behres, A., see Lakner, H. 170 (1997) 732
Benndorf, G., see Kirpal, G. 170 (1997) 167
Bergunde, T., M. Dauelsberg, L. Kadinski, Yu.N. Makarov, M. Weyers, D. Schmitz, G. Strauch and H. Jürgensen, Heat transfer and mass transport in a multiwafer MOVPE reactor: modelling and experimental studies 170 (1997) 66
Bergunde, T., see Kurpas, P. 170 (1997) 203
Bertone, D., A. Bricconi, R.Y. Fang, L. Greborio, G. Magnetti, M. Meliga and R. Paoletti, MOCVD regrowth of semi-insulating InP and p–n junction blocking layers around laser active stripes 170 (1997) 715
Bertram, F., see Heinrichsdorff, F. 170 (1997) 568
Bevan, M.J., H.D. Shih, H.Y. Liu, A.J. Syllaios and W.M. Duncan, Growth of high quality ZnSe on closely lattice-matched InGaAs substrates by metal organic chemical vapor deposition 170 (1997) 467
Beyer, R., see Prösch, G. 170 (1997) 537
Bhat, I.B., see Dakshina Murthy, S. 170 (1997) 193

ELSEVIER

Journal of Crystal Growth 170 (1997) 822–833

JOURNAL OF CRYSTAL GROWTH

# Author index

Adam, D., see Ortion, J.M. 170 (1997) 674
Adler, F., see Geiger, M. 170 (1997) 558
Ahern, B.S., see Weyburne, D.W. 170 (1997) 77
Aiga, M., see Takiguchi, T. 170 (1997) 705
Aina, L., see Thompson, A.G. 170 (1997) 92
Alexander, W.B., see Wickenden, A.E. 170 (1997) 367
Ambacher, O., see Fischer, R.A. 170 (1997) 139
Ambacher, O., R. Dimitrov, D. Lentz, T. Metzger, W. Rieger and M. Stutzmann, Growth of GaN/AlN and AlGaN by MOCVD using triethylgallium and tritertiarybutylaluminium 170 (1997) 335
Anand, S., see Carlsson, N. 170 (1997) 127
Anders, M.J., see Hageman, P.R. 170 (1997) 270
Anders, M.J., see Bastos, P.L. 170 (1997) 710
Ando, H., Recent progress in multi-wafer CBE systems 170 (1997) 16
Ando, H., see Ando, S. 170 (1997) 719
Ando, S., N. Kobayashi, H. Ando and Y. Horikoshi, Hexagonal facet laser with optical waveguides grown by flow-rate modulation epitaxy 170 (1997) 719
Aoki, M., see Suzuki, M. 170 (1997) 661
Aoki, S., see Funato, M. 170 (1997) 276
Aoyagi, Y., see Tanaka, S. 170 (1997) 329
Arai, T., J. Hidaka, H. Tokunaga and K. Matsumoto, Highly uniform growth in a low-pressure MOVPE multiple wafer system 170 (1997) 88
Arakawa, Y., see Kitamura, M. 170 (1997) 563
Arès, R., S.P. Watkins and C.A. Tran, Breakdown of self-limiting behaviour in InAs/GaAs heterostructures grown by atomic layer epitaxy 170 (1997) 574
Arès, R., see Watkins, S.P. 170 (1997) 788
Armour, E., see Thompson, A.G. 170 (1997) 92
Ayers, J.E., see Bao, K.X. 170 (1997) 497

Baker, J.E., see Islam, M.R. 170 (1997) 413
Bao, K.X., R. Mo, X.G. Zhang, S. Kalisetty, M. Gokhale, J. Robinson, G. Zhao, J.E. Ayers and F.C. Jain, Compositional control of $Cd_xZn_{1-x}Se$ grown by photoassisted organometallic vapor phase epitaxy 170 (1997) 497
Basilavecchia, M., see Gurskii, A.L. 170 (1997) 533
Baskar, K., see Soga, T. 170 (1997) 447
Bastos, P.L., M.J. Anders, M.M.G. Bongers, P.R. Hageman and L.J. Giling, Temperature dependence on the emerging crystal habit of GaInP deposited on nonplanar {001}GaAs substrates 170 (1997) 710
Bauknecht, A., see Geiger, M. 170 (1997) 558
Baumeister, H., see Keidler, M. 170 (1997) 161
Beaumont, B., M. Vaille, T. Boufaden, B. el Jani and P. Gibart, High quality GaN grown by MOVPE 170 (1997) 316
Beccard, R., G. Lengeling, D. Schmitz, Y. Gigase and H. Jürgensen, Replacement of hydrides by TBAs and TBP for the growth of various III–V materials in production scale MOVPE reactors 170 (1997) 97
Becht, M., F. Wang, J.G. Wen and T. Morishita, Evolution of the microstructure of oxide thin films 170 (1997) 799
Beckham, C., see Thompson, A.G. 170 (1997) 92
Behet, M., see Tümmler, J. 170 (1997) 772
Behet, M., see von Eichel-Streiber, C. 170 (1997) 783
Behres, A., H. Werner, A. Kohl and K. Heime, InP growth on ion-implanted InP substrate: a new method to achieve selective area MOVPE 170 (1997) 655
Behres, A., see Lakner, H. 170 (1997) 732
Benndorf, G., see Kirpal, G. 170 (1997) 167
Bergunde, T., M. Dauelsberg, L. Kadinski, Yu.N. Makarov, M. Weyers, D. Schmitz, G. Strauch and H. Jürgensen, Heat transfer and mass transport in a multiwafer MOVPE reactor: modelling and experimental studies 170 (1997) 66
Bergunde, T., see Kurpas, P. 170 (1997) 203
Bertone, D., A. Bricconi, R.Y. Fang, L. Greborio, G. Magnetti, M. Meliga and R. Paoletti, MOCVD regrowth of semi-insulating InP and p–n junction blocking layers around laser active stripes 170 (1997) 715
Bertram, F., see Heinrichsdorff, F. 170 (1997) 568
Bevan, M.J., H.D. Shih, H.Y. Liu, A.J. Syllaios and W.M. Duncan, Growth of high quality ZnSe on closely lattice-matched InGaAs substrates by metal organic chemical vapor deposition 170 (1997) 467
Beyer, R., see Prösch, G. 170 (1997) 537
Bhat, I.B., see Dakshina Murthy, S. 170 (1997) 193

Bhattacharya, A., see Mawst, L.J. 170 (1997) 383
Biasiol, G., E. Martinet, F. Reinhardt, A. Gustafsson and E. Kapon, Low-pressure OMCVD growth of AlGaAs vertical quantum wells on non-planar substrates 170 (1997) 600
Biasiol, G., see Reinhardt, F. 170 (1997) 689
Bimberg, D., see Dadgar, A. 170 (1997) 173
Bimberg, D., see Heinrichsdorff, F. 170 (1997) 568
Bimberg, D., see Kappelt, M. 170 (1997) 590
Biwa, G., see Yaguchi, H. 170 (1997) 353
Blumberg, R., see Kastner, M.J. 170 (1997) 188
Blumberg, R., see Hahn, B. 170 (1997) 472
Bolay, H., see Scholz, F. 170 (1997) 321
Bolognesi, C.R., see Watkins, S.P. 170 (1997) 788
Bongartz, M., see Hartmann, A. 170 (1997) 605
Bongers, M.M.G., see Bastos, P.L. 170 (1997) 710
Booker, G.R., M. Daly, P.C. Klipstein, M. Lakrimi, T.F. Kuech, Jiang Li, S.G. Lyapin, N.J. Mason, I.J. Murgatroyd, J.C. Portal, R.J. Nicholas, D.M. Symons, P. Vicente and P.J. Walker, Growth of InAs/GaSb strained layer superlattices by MOVPE. III. Use of UV absorption to monitor alkyl stability in the reactor 170 (1997) 777
Born, E., see Fischer, R.A. 170 (1997) 139
Botez, D., see Mawst, L.J. 170 (1997) 383
Boufaden, T., see Beaumont, B. 170 (1997) 316
Bouix, J., see Thévenot, V. 170 (1997) 251
Bricconi, A., see Bertone, D. 170 (1997) 715
Bromley, P.A., see Wood, A.K. 170 (1997) 132
Brunner, F., see Kurpas, P. 170 (1997) 442
Bruno, G., M. Losurdo and P. Capezzuto, On the use of remote RF plasma source to enhance III–V MOCVD technology 170 (1997) 301
Bryce, J.E., see Watkins, S.P. 170 (1997) 788
Bugge, F., see Knauer, A. 170 (1997) 281
Bullough, T.J., see Westwater, S.P. 170 (1997) 752
Burchard, A., see Lindner, A. 170 (1997) 287
Burghardt, H., see Prösch, G. 170 (1997) 537
Button, C.C., see Chen, Y.H. 170 (1997) 394

Capezzuto, P., see Bruno, G. 170 (1997) 301
Capik, R.J., see Wajid, A. 170 (1997) 237
Carlsson, N., see Seifert, W. 170 (1997) 39
Carlsson, N., S. Anand, S.-B. Carlsson, B. Gustafson, P. Omling, P. Ramvall, L. Samuelson, W. Seifert and Q. Wang, MOVPE growth of InP/GaInAs and GaAs/GaInP heterostructures for electronic transport applications 170 (1997) 127
Carlsson, S.-B., see Carlsson, N. 170 (1997) 127
Carr, N., see Wood, A.K. 170 (1997) 132
Case, F.C., see Mitra, P. 170 (1997) 542
Cerva, H., see Kappelt, M. 170 (1997) 590
Champagne, M., see Ortion, J.M. 170 (1997) 674
Chelakara, R.V., P.A. Grudowski and R.D. Dupuis, Design and growth of InAlAs/InGaAlAs strained-superlattice-barrier heterostructures for use in light-emitting devices 170 (1997) 595
Chen, C., see Chen, S. 170 (1997) 433
Chen, J.C., see Huang, Z.C. 170 (1997) 362
Chen, J.C., see Lee, K.-J. 170 (1997) 757
Chen, L., see Chen, S. 170 (1997) 433
Chen, S., B. Liu, B. Wang, M. Huang, L. Chen and C. Chen, GaAs–InP heteroepitaxy and GaAs–InP MESFET fabrication by MOVPE 170 (1997) 433
Chen, Y.H., C.I. Wilkinson, J. Woodhead, J.P.R. David, C.C. Button and P.N. Robson, Polarisation characteristics of visible VCSELs 170 (1997) 394
Chen, Y.H., see Roberts, J.S. 170 (1997) 621
Cheng, C.-C., see Liu, W.-C. 170 (1997) 438
Chichibu, S., see Kamata, A. 170 (1997) 518
Christen, J., see Heinrichsdorff, F. 170 (1997) 568
Chun, Y.S., H. Murata, I.H. Ho, T.C. Hsu and G.B. Stringfellow, Use of V/III ratio to produce heterostructures in ordered GaInP 170 (1997) 263
Chunggaze, M., see O'Brien, P. 170 (1997) 23
Clark, A., R.J. Egan and C. Jagadish, Design and optimisation of $Al_yGa_{1-y}As/Al_yGa_{1-y}As$ multilayer structures for visible wavelength applications 170 (1997) 424
Cole-Hamilton, D.J., see Pickett, N.L. 170 (1997) 476
Cole-Hamilton, D.J., see Fan, G.H. 170 (1997) 485
Colpitts, T., see Venkatasubramanian, R. 170 (1997) 817
Cordier, Y., see Ortion, J.M. 170 (1997) 674
Coulas, D., see Maigné, P. 170 (1997) 743
Crawley, J.A., see Zhang, X. 170 (1997) 83
Crawley, J.A., see Van der Stricht, W. 170 (1997) 344
Curtis, A.P., see Islam, M.R. 170 (1997) 413

Dadgar, A., L. Köhne, J.Y. Hyeon, T. Grundemann, O. Stenzel, M. Strassburg, M. Kuttler, R. Heitz, D. Bimberg and H. Schumann, 4d- and 5d-transition metal acceptor doping of InP 170 (1997) 173
Daguet, C., see Silvestre, L. 170 (1997) 639
Dakshina Murthy, S. and I.B. Bhat, In situ monitoring of CdTe nucleation on GaAs (100) using spectroscopic ellipsometry 170 (1997) 193
Daly, M., see Booker, G.R. 170 (1997) 777
Dauelsberg, M., see Bergunde, T. 170 (1997) 66
David, J.P.R., see Chen, Y.H. 170 (1997) 394
David, J.P.R., see Sale, T.E. 170 (1997) 399
David, J.P.R., see Roberts, J.S. 170 (1997) 621
Deicher, M., see Lindner, A. 170 (1997) 287
Delprat, D., see Silvestre, L. 170 (1997) 639
Delprat, D., see Zimmermann, G. 170 (1997) 645
Demeester, P., see Zhang, X. 170 (1997) 83
Demeester, P., see Van der Stricht, W. 170 (1997) 344
Demeester, P., see D'Hondt, M. 170 (1997) 616
Demeester, P., see Vanderbauwhede, W. 170 (1997) 738
DenBaars, S.P., see Kapolnek, D. 170 (1997) 340
DenBaars, S.P., see Keller, S. 170 (1997) 349

DeSisto, W.J. and B.J. Rappoli, In-line UV spectroscopy of $YBa_2Cu_3O_7$ MOCVD precursors 170 (1997) 242
Detchprohm, T., see Ohuchi, Y. 170 (1997) 325
Deufel, M., see Hahn, B. 170 (1997) 472
D'Hondt, M., I. Moerman and P. Demeester, Characterisation of 2% mismatched InGaAs and InAsP layers, grown on different buffer layers and at different growth temperatures 170 (1997) 616
Dieker, Ch., see Hartmann, A. 170 (1997) 605
Dimitrov, R., see Ambacher, O. 170 (1997) 335
Dörnen, A., see Scholz, F. 170 (1997) 321
Drews, D., see Schneider, A. 170 (1997) 767
Drigo, A.V., see Mazzer, M. 170 (1997) 553
Druilhe, R., see Tromson-Carli, A. 170 (1997) 549
Duan, S.-k. and D.-c. Lu, Phase diagrams for the MOVPE growth of ZnTe and ZnSeTe 170 (1997) 514
Duc, T.-M., see Thévenot, V. 170 (1997) 251
Dumont, H., see Thévenot, V. 170 (1997) 251
Duncan, W.M., see Bevan, M.J. 170 (1997) 467
Dupuis, R.D., see Islam, M.R. 170 (1997) 413
Dupuis, R.D., see Chelakara, R.V. 170 (1997) 595
Duschl, R., see Kastner, M.J. 170 (1997) 188
Dwir, B., see Reinhardt, F. 170 (1997) 689

Egan, R.J., see Clark, A. 170 (1997) 424
Eisenbach, A., A. Goldhorn, E. Kuphal and K. Mause, MOVPE growth for an integrated InGaAs/InP PIN-HBT receiver using Zn-doped $p^+$-InGaAs layers 170 (1997) 451
Ekawa, M., T. Fujii and T. Tanahashi, Effect of incorporation efficiency on dopant behaviors in selective-area metalorganic vapor phase epitaxy 170 (1997) 685
El-Masry, N., see Venkatasubramanian, R. 170 (1997) 817
El Jani, B., see Beaumont, B. 170 (1997) 316
Ellmer, K., see Thomas, B. 170 (1997) 808
Epler, J., see Moser, M. 170 (1997) 404
Ernst, P., see Geng, C. 170 (1997) 418
Ertel, J., see Tromson-Carli, A. 170 (1997) 549
Esser, N., see Knorr, K. 170 (1997) 230
Evans, D.A., see Gnoth, D.N. 170 (1997) 198
Evrard, R., see Gurskii, A.L. 170 (1997) 533

Fan, G.H., N. Maung, T.L. Ng, P.F. Heelis, J.O. Williams, A.C. Wright, D.F. Foster and D.J. Cole-Hamilton, Thermal decomposition of di-tertiarybutyl selenide and dimethylzinc in a metalorganic vapour phase epitaxy reactor 170 (1997) 485
Fang, R.Y., see Bertone, D. 170 (1997) 715
Fiechter, S., see Thomas, B. 170 (1997) 808
Fischer, R.A., A. Miehr, O. Ambacher, T. Metzger and E. Born, Novel single source precursors for MOCVD of AlN, GaN and InN 170 (1997) 139
Flavell, W.R., see Yates, H.M. 170 (1997) 611
Foster, D.F., see Pickett, N.L. 170 (1997) 476
Foster, D.F., see Fan, G.H. 170 (1997) 485
Franke, D. and H. Roehle, Highly reproducible and defect-free MOVPE overgrowth of InGaAsP-based DFB gratings 170 (1997) 113
Frankowsky, G., see Ottenwälder, D. 170 (1997) 695
Franzheld, R., see Kirpal, G. 170 (1997) 167
Freitag, S., see Pohl, U.W. 170 (1997) 144
Freitas Jr., J.A., see Wickenden, A.E. 170 (1997) 367
Fujii, K., K. Shimoyama, N. Hosoi, K. Kiyomi, A. Yamauchi and H. Gotoh, Dependence of deposition selectivity for MOVPE of AlGaAs using HCl gas on the orientation of the substrate and the orientation of the stripe of $SiN_x$ masks 170 (1997) 679
Fujii, T., see Ekawa, M. 170 (1997) 685
Fujita, Sg., see Funato, M. 170 (1997) 276
Fujita, Sg., see Ogata, K.-i. 170 (1997) 507
Fujita, Sz., see Funato, M. 170 (1997) 276
Fujita, Sz., see Ogata, K.-i. 170 (1997) 507
Fukui, T., see Hara, S. 170 (1997) 579
Fukui, T., see Kumakura, K. 170 (1997) 700
Funato, M., S. Aoki, Sz. Fujita and Sg. Fujita, Initial growth behavior of GaAs on ZnSe in MOVPE 170 (1997) 276

Garcia, J.C., see Ortion, J.M. 170 (1997) 674
Gardner, N.F., see Islam, M.R. 170 (1997) 413
Gebhardt, W., see Kastner, M.J. 170 (1997) 188
Gebhardt, W., see Hahn, B. 170 (1997) 472
Geiger, M., A. Bauknecht, F. Adler, H. Schweizer and F. Scholz, Observation of the 2D–3D growth mode transition in the InAs/GaAs system 170 (1997) 558
Geng, C., A. Moritz, S. Heppel, A. Mühe, J. Kuhn, P. Ernst, H. Schweizer, F. Phillipp, A. Hangleiter and F. Scholz, Influence of order-domain size on the optical gain of AlGaInP laser structures 170 (1997) 418
Gerhardt, M., see Kirpal, G. 170 (1997) 167
Germain, M., see Gurskii, A.L. 170 (1997) 533
Geurts, J., see Tümmler, J. 170 (1997) 772
Gfrörer, O., see Ottenwälder, D. 170 (1997) 695
Gibart, P., see Beaumont, B. 170 (1997) 316
Gigase, Y., see Beccard, R. 170 (1997) 97
Giling, L.J., see Hageman, P.R. 170 (1997) 270
Giling, L.J., see Bastos, P.L. 170 (1997) 710
Gloukhian, A., see Zimmermann, G. 170 (1997) 645
Gnoth, D.N., I.B. Poole, T.L. Ng, D.A. Evans, N. Maung, J.O. Williams and A.C. Wright, Growth process studies by reflectance anisotropy spectroscopy on MOVPE ZnSe 170 (1997) 198
Göbel, E.O., see Protzmann, H. 170 (1997) 155
Göbel, E.O., see Spika, Z. 170 (1997) 257
Göbel, E.O., see Rettig, R. 170 (1997) 748
Gogol, C., see Wajid, A. 170 (1997) 237
Gokhale, M., see Bao, K.X. 170 (1997) 497
Goldhorn, A., see Eisenbach, A. 170 (1997) 451
Goto, H., M. Takemura and T. Ido, Deep hole trap level of nitrogen-doped ZnSe grown by metalorganic vapor phase epitaxy 170 (1997) 510

Goto, K., see Takiguchi, T. 170 (1997) 705
Gotoh, H., see Fujii, K. 170 (1997) 679
Gotoh, S., see Nakamura, K. 170 (1997) 377
Gottfriedsen, J., see Pohl, U.W. 170 (1997) 144
Gottschalch, V., see Kirpal, G. 170 (1997) 167
Grahn, H.T., see Hatatani, S. 170 (1997) 297
Gramlich, S., see Knauer, A. 170 (1997) 281
Grattepain, C., see Tromson-Carli, A. 170 (1997) 549
Greborio, L., see Bertone, D. 170 (1997) 715
Griffiths, C.L., see Stafford, A. 170 (1997) 182
Grudowski, P.A., see Chelakara, R.V. 170 (1997) 595
Grundemann, T., see Dadgar, A. 170 (1997) 173
Grundmann, M., see Heinrichsdorff, F. 170 (1997) 568
Grundmann, M., see Kappelt, M. 170 (1997) 590
Gulden, K.H., see Moser, M. 170 (1997) 404
Guo, L.-Q., see Hatatani, S. 170 (1997) 297
Gurskii, A.L., W. Taudt, S. Lampe, H. Hamadeh, F. Sauerländer, M. Germain, M. Basilavecchia, R. Evrard, G.P. Yablonskii and M. Heuken, Optical and electrical properties of MOVPE-grown ZnSe:N using triallylamine as a nitrogen precursor 170 (1997) 533
Gustafson, B., see Carlsson, N. 170 (1997) 127
Gustafsson, A., see Biasiol, G. 170 (1997) 600
Gutsche, D., see Kurpas, P. 170 (1997) 442

Hageman, P.R., J. te Nijenhuis, M.J. Anders and L.J. Giling, Dependence of impurity incorporation upon substrate misorientation during GaAs growth by metalorganic vapour phase epitaxy 170 (1997) 270
Hageman, P.R., see Bastos, P.L. 170 (1997) 710
Hahn, B., see Kastner, M.J. 170 (1997) 188
Hahn, B., M. Deufel, M. Meier, M.J. Kastner, R. Blumberg and W. Gebhardt, Photoassisted growth and nitrogen doping of ZnSe 170 (1997) 472
Halliwell, M.A.G., X-ray diffraction solutions to heteroepitaxial growth problems 170 (1997) 47
Hamadeh, H., see Heuken, M. 170 (1997) 30
Hamadeh, H., see Taudt, W. 170 (1997) 491
Hamadeh, H., see Gurskii, A.L. 170 (1997) 533
Han, Y.K., see Kim, E.K. 170 (1997) 803
Hanamaki, Y., see Pan, W. 170 (1997) 585
Haneda, S., see Nishida, K. 170 (1997) 312
Hangleiter, A., see Scholz, F. 170 (1997) 321
Hangleiter, A., see Geng, C. 170 (1997) 418
Hangleiter, A., see Ottenwälder, D. 170 (1997) 695
Hara, K., see Nishida, K. 170 (1997) 312
Hara, K., see Honda, T. 170 (1997) 503
Hara, S., J. Motohisa and T. Fukui, Formation and characterization of InGaAs strained quantum wires on GaAs multiatomic steps grown by metalorganic vapor phase epitaxy 170 (1997) 579
Hardt, A., see Taudt, W. 170 (1997) 491
Hardtdegen, H., see Hollfelder, M. 170 (1997) 103
Hardtdegen, H., see Hartmann, A. 170 (1997) 605
Härle, V., see Scholz, F. 170 (1997) 321
Hartmann, A., M. Bongartz, M. Hollfelder, H. Hardtdegen, Ch. Dieker and H. Lüth, Growth of modulation-doped GaAs/AlGaAs quantum wires on V-groove patterned substrates 170 (1997) 605
Hasumi, H., see Sakata, Y. 170 (1997) 456
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Heime, K., see Behres, A. 170 (1997) 655
Heime, K., see Lakner, H. 170 (1997) 732
Heime, K., see Tümmler, J. 170 (1997) 772
Heime, K., see von Eichel-Streiber, C. 170 (1997) 783
Heinecke, H., see Ritter, D. 170 (1997) 149
Heinecke, H., see Keidler, M. 170 (1997) 161
Heinrichsdorff, F., A. Krost, M. Grundmann, D. Bimberg, F. Bertram, J. Christen, A. Kosogov and P. Werner, Self organization phenomena of InGaAs/GaAs quantum dots grown by metalorganic chemical vapour deposition 170 (1997) 568
Heitz, R., see Dadgar, A. 170 (1997) 173
Hellig, K., see Prösch, G. 170 (1997) 537
Heppel, S., see Geng, C. 170 (1997) 418
Hermans, J., see Tümmler, J. 170 (1997) 772
Hetzel, M., see Wajid, A. 170 (1997) 237
Heuken, M., J. Söllner, W. Taudt, S. Lampe and H. Hamadeh, Metalorganic chemical vapor epitaxy and doping of ZnMgSSe heterostructures for blue emitting devices 170 (1997) 30
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Heuken, M., see Gurskii, A.L. 170 (1997) 533
Heuken, M., see Prösch, G. 170 (1997) 537
Heuken, M., see Schneider, A. 170 (1997) 767
Heuken, M., see von Eichel-Streiber, C. 170 (1997) 783
Hidaka, J., see Arai, T. 170 (1997) 88
Hiramatsu, K., see Ohuchi, Y. 170 (1997) 325
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Ho, I.H., see Murata, H. 170 (1997) 219
Ho, I.H., see Chun, Y.S. 170 (1997) 263
Höhnsdorf, F., see Protzmann, H. 170 (1997) 155
Hollfelder, M., S. Hon, B. Setzer, K. Schimpf, M. Horstmann, Th. Schäpers, D. Schmitz, H. Hardtdegen and H. Lüth, Demonstration of the $N_2$ carrier process for LP-MOVPE of III/V's 170 (1997) 103
Hollfelder, M., see Hartmann, A. 170 (1997) 605
Holmes, A.L., see Islam, M.R. 170 (1997) 413
Hon, S., see Hollfelder, M. 170 (1997) 103

Honda, T., S.W. Lim, K. Inoue, K. Hara, H. Munekata, H. Kukimoto, F. Koyama and K. Iga, Diode characteristics of $Li_3N$-diffused ZnSe grown by MOVPE 170 (1997) 503
Höpfner, C., see Thomas, B. 170 (1997) 808
Horikawa, H., see Nakamura, K. 170 (1997) 377
Horikoshi, Y., see Ando, S. 170 (1997) 719
Horstmann, M., see Hollfelder, M. 170 (1997) 103
Hosoi, N., see Fujii, K. 170 (1997) 679
Hsu, T.C., see Chun, Y.S. 170 (1997) 263
Huang, M., see Chen, S. 170 (1997) 433
Huang, Z.C., J.C. Chen and D. Wickenden, Characterization of GaN using thermally stimulated current and photocurrent spectroscopies and its application to UV detectors 170 (1997) 362
Hull, R., see Islam, M.R. 170 (1997) 413
Hurd, C., see Wajid, A. 170 (1997) 237
Hwang, S.-M., see Kim, S.-I. 170 (1997) 665
Hyeon, J.Y., see Dadgar, A. 170 (1997) 173
Hyuga, F., see Nittono, T. 170 (1997) 762

Ido, T., see Goto, H. 170 (1997) 510
Iga, K., see Honda, T. 170 (1997) 503
Ingle, N.K., see Theodoropoulos, C. 170 (1997) 72
Inomoto, Y., see Sakata, Y. 170 (1997) 456
Inoue, K., see Honda, T. 170 (1997) 503
Irvine, S.J.C., see Stafford, A. 170 (1997) 182
Ishibashi, A., see Toda, A. 170 (1997) 461
Ishikawa, M., see Pan, W. 170 (1997) 585
Ishino, M., see Otsuka, N. 170 (1997) 626
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Itagaki, T., see Takiguchi, T. 170 (1997) 705
Ito, R., see Yaguchi, H. 170 (1997) 353
Ito, R., see Pan, W. 170 (1997) 585
Iwai, S., see Tanaka, S. 170 (1997) 329

Jagadish, C., see Clark, A. 170 (1997) 424
Jain, F.C., see Bao, K.X. 170 (1997) 497
Jansen, M., see Mawst, L.J. 170 (1997) 383
Jensen, K.F., see Wang, C.A. 170 (1997) 55
Jiang, J., see Spika, Z. 170 (1997) 257
Jimbo, T., see Soga, T. 170 (1997) 447
Johansson, J., see Seifert, W. 170 (1997) 39
Johnson, N.P., see Yates, H.M. 170 (1997) 611
Jones, A.C., see O'Brien, P. 170 (1997) 23
Jones, A.C., see Wang, C.A. 170 (1997) 55
Jürgensen, H., see Bergunde, T. 170 (1997) 66
Jürgensen, H., see Beccard, R. 170 (1997) 97

Kadinski, L., see Bergunde, T. 170 (1997) 66
Kaiser, R., see Roehle, H. 170 (1997) 109
Kalisetty, S., see Bao, K.X. 170 (1997) 497
Kamata, A., H. Yoshida, S. Chichibu and H. Nakanishi, Growth and doping characteristics of ZnSeTe epilayers by MOCVD 170 (1997) 518
Kaneda, N., see Ohuchi, Y. 170 (1997) 325
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Kato, T., see Hirotani, M. 170 (1997) 390
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Kaufmann, B., see Scholz, F. 170 (1997) 321
Kawaguchi, D., see Ogata, K.-i. 170 (1997) 507
Kearley, M.Q., see Wood, A.K. 170 (1997) 132
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Keller, B.P., see Kapolnek, D. 170 (1997) 340
Keller, B.P., see Keller, S. 170 (1997) 349
Keller, S., see Kapolnek, D. 170 (1997) 340
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Kera, T., see Ogata, K.-i. 170 (1997) 507
Kibune, M., see Yaguchi, H. 170 (1997) 353
Kim, E.K., see Kim, S.-I. 170 (1997) 665
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Kito, M., see Otsuka, N. 170 (1997) 626
Kiyomi, K., see Fujii, K. 170 (1997) 679
Klipstein, P.C., see Booker, G.R. 170 (1997) 777
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Kobayashi, N., see Kasu, M. 170 (1997) 246
Kobayashi, N., see Saito, H. 170 (1997) 372
Kobayashi, N., see Ando, S. 170 (1997) 719
Kobayashi, Y., see Kobayashi, N. 170 (1997) 225
Kohl, A., see Behres, A. 170 (1997) 655
Kohl, A., see Lakner, H. 170 (1997) 732
Köhne, L., see Dadgar, A. 170 (1997) 173
Kolbas, R.M., see Keller, S. 170 (1997) 349
Koleske, D.D., see Wickenden, A.E. 170 (1997) 367
Komori, M., see Suzuki, M. 170 (1997) 661
Konagai, M., see Hatatani, S. 170 (1997) 297
Kosogov, A., see Heinrichsdorff, F. 170 (1997) 568
Koukitu, A., N. Takahashi, T. Taki and H. Seki, Thermodynamic analysis of the MOVPE growth of $In_xGa_{1-x}N$ 170 (1997) 306
Koyama, F., see Honda, T. 170 (1997) 503
Kozyrkov, V.V., see Scriven, G.J. 170 (1997) 813
Krishnankutty, S., see Keller, S. 170 (1997) 349
Kroll, W., see Thompson, A.G. 170 (1997) 92
Krost, A., see Heinrichsdorff, F. 170 (1997) 568
Kudo, K., T. Sasaki and M. Yamaguchi, Migration-controlled narrow-stripe selective MOVPE for high-quality InGaAsP/InGaAsP MQWs 170 (1997) 634
Kuech, T.F., see Li, J. 170 (1997) 292
Kuech, T.F., see Liu, J. 170 (1997) 357
Kuech, T.F., see Booker, G.R. 170 (1997) 777
Kuhn, J., see Geng, C. 170 (1997) 418
Kukimoto, H., see Nishida, K. 170 (1997) 312
Kukimoto, H., see Honda, T. 170 (1997) 503
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Kuttler, M., see Dadgar, A. 170 (1997) 173

Lach, E., see Wiedemann, P. 170 (1997) 117
Laih, L.-W., see Liu, W.-C. 170 (1997) 438
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Lakrimi, M., see Booker, G.R. 170 (1997) 777
Lampe, S., see Heuken, M. 170 (1997) 30
Lampe, S., see Taudt, W. 170 (1997) 491
Lampe, S., see Gurskii, A.L. 170 (1997) 533
Lamvik, M., see Venkatasubramanian, R. 170 (1997) 817
Landgren, G., see Silfvenius, C. 170 (1997) 122
Laube, G., see Wiedemann, P. 170 (1997) 117
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Leitch, A.W.R., see Scriven, G.J. 170 (1997) 813
Lengeling, G., see Beccard, R. 170 (1997) 97
Lentz, D., see Ambacher, O. 170 (1997) 335
Leo, G., see Mazzer, M. 170 (1997) 553
Leys, M.R., see Verschuren, C.A. 170 (1997) 650
Li, J. and T.F. Kuech, Surface morphology of carbon-doped GaAs grown by MOVPE 170 (1997) 292
Li, J., see Booker, G.R. 170 (1997) 777
Lim, S.W., see Honda, T. 170 (1997) 503
Lin, K.-W., see Liu, W.-C. 170 (1997) 438
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Liu, B., see Chen, S. 170 (1997) 433
Liu, H.Y., see Bevan, M.J. 170 (1997) 467
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Longo, M., see Mazzer, M. 170 (1997) 553
Lopez, J., see Mawst, L.J. 170 (1997) 383
Lorberth, J., see Protzmann, H. 170 (1997) 155
Losurdo, M., see Bruno, G. 170 (1997) 301
Lovergine, N., see Mazzer, M. 170 (1997) 553
Lu, D.-c., see Duan, S.-k. 170 (1997) 514
Lum, R., see Wajid, A. 170 (1997) 237
Lüth, H., see Hollfelder, M. 170 (1997) 103
Lüth, H., see Hartmann, A. 170 (1997) 605
Lyapin, S.G., see Booker, G.R. 170 (1997) 777

Magerle, R., see Lindner, A. 170 (1997) 287
Magnetti, G., see Bertone, D. 170 (1997) 715
Maigné, P. and D. Coulas, Structural investigation of MOVPE grown InGaAs buffer layers 170 (1997) 743
Majerfeld, A., see Mao, E. 170 (1997) 428
Makarov, Yu.N., see Bergunde, T. 170 (1997) 66
Makimoto, T., see Saito, H. 170 (1997) 372
Makita, K., see Tsuji, M. 170 (1997) 669
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Malik, M.A., see O'Brien, P. 170 (1997) 23
Mancini, A.M., see Mazzer, M. 170 (1997) 553
Mao, E. and A. Majerfeld, Growth of heavily C-doped GaAs/AlGaAs MQW structures by MOVPE for 2–3 $\mu$m normal incidence photodetectors 170 (1997) 428
Marheineke, B., see Keidler, M. 170 (1997) 161
Marschner, T., see Rettig, R. 170 (1997) 748
Martin, R.W., see Wood, A.K. 170 (1997) 132
Martinet, E., see Biasiol, G. 170 (1997) 600
Mason, N.J., see Booker, G.R. 170 (1997) 777
Matsui, Y., see Otsuka, N. 170 (1997) 626
Matsumoto, K., see Arai, T. 170 (1997) 88
Mattocks, P.G., see Peck, J. 170 (1997) 523
Maung, N., see Gnoth, D.N. 170 (1997) 198
Maung, N., see Fan, G.H. 170 (1997) 485
Maung, N., see Poole, I.B. 170 (1997) 528
Mause, K., see Eisenbach, A. 170 (1997) 451
Mawst, L.J., A. Bhattacharya, M. Nesnidal, J. Lopez, D. Botez, A.V. Syrbu, V.P. Yakovlev, G.I. Suruceanu, A.Z. Mereutza, M. Jansen and R.F. Nabiev, MOVPE-grown high CW power InGaAs/InGaAsP/InGaP diode lasers 170 (1997) 383
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McDonald, M., see Wajid, A. 170 (1997) 237
Meier, M., see Hahn, B. 170 (1997) 472
Meliga, M., see Bertone, D. 170 (1997) 715
Mereutza, A.Z., see Mawst, L.J. 170 (1997) 383
Metzger, T., see Fischer, R.A. 170 (1997) 139
Metzger, T., see Ambacher, O. 170 (1997) 335
Miehr, A., see Fischer, R.A. 170 (1997) 139
Mihashi, Y., see Takiguchi, T. 170 (1997) 705
Min, B.-D., see Kim, S.-I. 170 (1997) 665
Min, S.-K., see Kim, S.-I. 170 (1997) 665
Min, S.-K., see Kim, E.K. 170 (1997) 803
Minagawa, S., see Suzuki, M. 170 (1997) 661
Mircea, A., see Zimmermann, G. 170 (1997) 645
Mishra, U.K., see Kapolnek, D. 170 (1997) 340
Mishra, U.K., see Keller, S. 170 (1997) 349
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Miyoshi, S., see Yaguchi, H. 170 (1997) 353
Mizuno, Y., S.-i. Uekusa and H. Okabe, Hydrodynamic description of epitaxial film growth in a horizontal reactor 170 (1997) 61
Mo, R., see Bao, K.X. 170 (1997) 497
Moerman, I., see Zhang, X. 170 (1997) 83
Moerman, I., see Van der Stricht, W. 170 (1997) 344
Moerman, I., see D'Hondt, M. 170 (1997) 616
Moerman, I., see Vanderbauwhede, W. 170 (1997) 738
Monteil, Y., see Thévenot, V. 170 (1997) 251
Moon, R.L., MOVPE: is there any other technology for optoelectronics? 170 (1997) 1
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Morishita, T., see Becht, M. 170 (1997) 799
Moritz, A., see Geng, C. 170 (1997) 418
Moseley, A.J., see Wood, A.K. 170 (1997) 132
Moser, M., K.H. Gulden, J. Epler and H.P. Schweizer, High performance deep red AlAs/AlGaAs top-emitting VCSELs grown by MOVPE at high growth rates 170 (1997) 404
Motohisa, J., see Hara, S. 170 (1997) 579
Motohisa, J., see Kumakura, K. 170 (1997) 700
Moulin, D., see Tümmler, J. 170 (1997) 772
Mountziaris, T.J., see Theodoropoulos, C. 170 (1997) 72
Mountziaris, T.J., see Peck, J. 170 (1997) 523
Mühe, A., see Geng, C. 170 (1997) 418
Müller, M., see Protzmann, H. 170 (1997) 155
Müller, M., see Thomas, B. 170 (1997) 808
Munekata, H., see Nishida, K. 170 (1997) 312
Munekata, H., see Honda, T. 170 (1997) 503
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Murata, H., see Chun, Y.S. 170 (1997) 263
Murgatroyd, I.J., see Booker, G.R. 170 (1997) 777

Nabiev, R.F., see Mawst, L.J. 170 (1997) 383
Nakahara, J., see Suemune, I. 170 (1997) 480
Nakajima, M., see Nakamura, K. 170 (1997) 377
Nakamura, F., see Toda, A. 170 (1997) 461
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Nakayama, H., see Ohuchi, Y. 170 (1997) 325
Nashiki, H., see Suemune, I. 170 (1997) 480
Neethling, J.H., see Scriven, G.J. 170 (1997) 813
Nesnidal, M., see Mawst, L.J. 170 (1997) 383
Ng, T.L., see Gnoth, D.N. 170 (1997) 198
Ng, T.L., see Fan, G.H. 170 (1997) 485
Ng, T.L., see Poole, I.B. 170 (1997) 528
Nicholas, R.J., see Wood, A.K. 170 (1997) 132
Nicholas, R.J., see Booker, G.R. 170 (1997) 777
Ninomiya, T., see Ohkubo, M. 170 (1997) 177
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Okabe, H., see Mizuno, Y. 170 (1997) 61
Omling, P., see Carlsson, N. 170 (1997) 127
Onabe, K., see Yaguchi, H. 170 (1997) 353
Onabe, K., see Pan, W. 170 (1997) 585
Opitz, B., see Lakner, H. 170 (1997) 732
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Oshiba, S., see Nakamura, K. 170 (1997) 377
Oster, A., see Knauer, A. 170 (1997) 281
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Ougazzaden, A., see Zimmermann, G. 170 (1997) 645

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Paoletti, R., see Bertone, D. 170 (1997) 715
Patriarche, G., see Silvestre, L. 170 (1997) 639
Patrikarakos, D.G., N. Shukla and M.E. Pemble, Reflectance anisotropy as an in situ monitor for the growth of InP on (001) InP by pseudo-atmospheric pressure atomic layer epitaxy 170 (1997) 215
Peck, J., T.J. Mountziaris, S. Stoltz, A. Petrou and P.G. Mattocks, Metalorganic vapor phase epitaxy of $Zn_{1-x}Fe_xSe$ films 170 (1997) 523
Pemble, M.E., see Patrikarakos, D.G. 170 (1997) 215
Pemble, M.E., see Yates, H.M. 170 (1997) 611
Petrou, A., see Peck, J. 170 (1997) 523
Phillipp, F., see Geng, C. 170 (1997) 418
Pickett, N.L., D.F. Foster and D.J. Cole-Hamilton, Studies of prereactions during MOVPE growth of wide band-gap II/VI semiconductors: the effect of pyridine upon the gas-phase reactions between $H_2S$ and $Me_2Zn$ 170 (1997) 476
Pietag, F., see Kirpal, G. 170 (1997) 167
Pietzonka, I., see Kirpal, G. 170 (1997) 167
Pistol, M.-E., see Seifert, W. 170 (1997) 39
Pohl, U.W., S. Freitag, J. Gottfriedsen, W. Richter and H. Schumann, Synthesis and properties of zinc–nitrogen compounds for the MOVPE of p-type ZnSe 170 (1997) 144
Poole, I.B., see Gnoth, D.N. 170 (1997) 198
Poole, I.B., T.L. Ng, N. Maung, J.O. Williams and A.C. Wright, MOVPE growth of magnesium cadmium sulphide: rocksalt or sphalerite? 170 (1997) 528
Popp, M., see Keidler, M. 170 (1997) 161
Portal, J.C., see Booker, G.R. 170 (1997) 777

Pristovsek, M., see Knorr, K. 170 (1997) 230

Prösch, G., K. Hellig, R. Beyer, A. Schneider, H. Burghardt, W. Taudt, M. Heuken and D.R.T. Zahn, Defects in MOVPE grown ZnSe on GaAs studied by deep level transient spectroscopy 170 (1997) 537

Prost, W., see Lindner, A. 170 (1997) 287

Protzmann, H., F. Höhnsdorf, Z. Spika, W. Stolz, E.O. Göbel, M. Müller and J. Lorberth, Properties of $(Ga_{0.47}In_{0.53})As$ epitaxial layers grown by metalorganic vapor phase epitaxy (MOVPE) using alternative arsenic precursors 170 (1997) 155

Ramdane, A., see Silvestre, L. 170 (1997) 639

Ramdane, A., see Zimmermann, G. 170 (1997) 645

Ramvall, P., see Carlsson, N. 170 (1997) 127

Rao, E.V.K., see Zimmermann, G. 170 (1997) 645

Rappoli, B.J., see DeSisto, W.J. 170 (1997) 242

Rechenberg, I., see Knauer, A. 170 (1997) 281

Redwing, J.M., see Liu, J. 170 (1997) 357

Regreny, P., see Thévenot, V. 170 (1997) 251

Reine, M.B., see Mitra, P. 170 (1997) 542

Reinhardt, F., see Biasiol, G. 170 (1997) 600

Reinhardt, F., B. Dwir, G. Biasiol and E. Kapon, Step ordering during OMCVD growth on non-planar substrates 170 (1997) 689

Resch-Esser, U., see Knorr, K. 170 (1997) 230

Rettig, R., T. Marschner, L. Tapfer, W. Stolz and E.O. Göbel, Growth and structural properties of (GaIn)As/Ga(PAs) intentionally disordered superlattice structures grown by metalorganic vapor phase epitaxy 170 (1997) 748

Richter, E., see Kurpas, P. 170 (1997) 442

Richter, W., see Pohl, U.W. 170 (1997) 144

Richter, W., see Kurpas, P. 170 (1997) 203

Richter, W., see Steimetz, E. 170 (1997) 208

Richter, W., see Knorr, K. 170 (1997) 230

Rieger, W., see Ambacher, O. 170 (1997) 335

Ritter, D. and H. Heinecke, Evaluation of cracking efficiency of As and P precursors 170 (1997) 149

Ritter, D., see Keidler, M. 170 (1997) 161

Roberts, J.S., see Hirotani, M. 170 (1997) 390

Roberts, J.S., see Sale, T.E. 170 (1997) 399

Roberts, J.S., J.P.R. David, Y.H. Chen and T.E. Sale, Optical properties of MOVPE grown $Al_xGa_{1-x}As$ quantum wells 170 (1997) 621

Robinson, J., see Bao, K.X. 170 (1997) 497

Robson, P.N., see Hirotani, M. 170 (1997) 390

Robson, P.N., see Chen, Y.H. 170 (1997) 394

Robson, P.N., see Sale, T.E. 170 (1997) 399

Roehle, H., H. Schroeter-Janssen and R. Kaiser, Large- and selective-area LP-MOVPE growth of InGaAsP-based bulk and QW layers under nitrogen atmosphere 170 (1997) 109

Roehle, H., see Franke, D. 170 (1997) 113

Romanato, F., see Mazzer, M. 170 (1997) 553

Romanov, S.G., see Yates, H.M. 170 (1997) 611

Rongen, R.T.H., see Verschuren, C.A. 170 (1997) 650

Rumberg, A., see Kurpas, P. 170 (1997) 203

Saito, H., T. Makimoto and N. Kobayashi, Photoluminescence characteristics of nitrogen atomic-layer-doped GaAs grown by MOVPE 170 (1997) 372

Saka, T., see Hirotani, M. 170 (1997) 390

Sakata, Y., T. Morimoto, Y. Inomoto and H. Hasumi, Low-threshold strained multi-quantum well lasers fabricated by selective metalorganic vapor phase epitaxy without a semiconductor etching process 170 (1997) 456

Sale, T.E., see Hirotani, M. 170 (1997) 390

Sale, T.E., J.S. Roberts, J. Woodhead, J.P.R. David and P.N. Robson, Visible (683 to 713 nm) room-temperature AlGaAs vertical cavity surface emitting lasers (VCSELs) 170 (1997) 399

Sale, T.E., see Roberts, J.S. 170 (1997) 621

Salim, S., see Wang, C.A. 170 (1997) 55

Salviati, G., see Mazzer, M. 170 (1997) 553

Samuelson, L., see Seifert, W. 170 (1997) 39

Samuelson, L., see Carlsson, N. 170 (1997) 127

Sasaki, T., see Kudo, K. 170 (1997) 634

Sato, H., see Suzuki, M. 170 (1997) 661

Sato, M., see Kurpas, P. 170 (1997) 203

Sato, M., see Kurpas, P. 170 (1997) 442

Sauerländer, F., see Gurskii, A.L. 170 (1997) 533

Sawaki, N., see Ohuchi, Y. 170 (1997) 325

Schaper, A., see Spika, Z. 170 (1997) 257

Schäpers, Th., see Hollfelder, M. 170 (1997) 103

Schienle, F., see Steimetz, E. 170 (1997) 208

Schimpf, K., see Hollfelder, M. 170 (1997) 103

Schmitz, D., see Bergunde, T. 170 (1997) 66

Schmitz, D., see Beccard, R. 170 (1997) 97

Schmitz, D., see Hollfelder, M. 170 (1997) 103

Schneider, A., see Prösch, G. 170 (1997) 537

Schneider, A., D. Drews, J. Söllner, M. Heuken and D.R.T. Zahn, Temperature induced resonant Raman scattering of MOVPE grown $ZnS_xSe_{1-x}/GaAs(100)$ heterostructures 170 (1997) 767

Schneider, P., see Tümmler, J. 170 (1997) 772

Scholz, F., V. Härle, F. Steuber, H. Bolay, A. Dörnen, B. Kaufmann, V. Syganow and A. Hangleiter, Low pressure MOVPE of GaN and GaInN/GaN heterostructures 170 (1997) 321

Scholz, F., see Geng, C. 170 (1997) 418

Scholz, F., see Geiger, M. 170 (1997) 558

Scholz, F., see Ottenwälder, D. 170 (1997) 695

Schroeter-Janssen, H., see Roehle, H. 170 (1997) 109

Schumann, H., see Pohl, U.W. 170 (1997) 144

Schumann, H., see Dadgar, A. 170 (1997) 173

Schur, R., see Kitamura, M. 170 (1997) 563

Schwabe, R., see Kirpal, G. 170 (1997) 167

Schweizer, H., see Geng, C. 170 (1997) 418

Schweizer, H., see Geiger, M. 170 (1997) 558

Schweizer, H.P., see Moser, M. 170 (1997) 404

Scriven, G.J., A.W.R. Leitch, J.H. Neethling, V.V. Kozyrkov and V.J. Watters, The growth of $Zn_3As_2$ on InP by atmospheric pressure MOVPE 170 (1997) 813
Seibt, M., see Tromson-Carli, A. 170 (1997) 549
Seifert, W., N. Carlsson, J. Johansson, M.-E. Pistol and L. Samuelson, In situ growth of nano-structures by metal-organic vapour phase epitaxy 170 (1997) 39
Seifert, W., see Carlsson, N. 170 (1997) 127
Seki, H., see Koukitu, A. 170 (1997) 306
Setzer, B., see Hollfelder, M. 170 (1997) 103
Shao, C.L., see Soga, T. 170 (1997) 447
Shibata, K., see Takiguchi, T. 170 (1997) 705
Shih, H.D., see Bevan, M.J. 170 (1997) 467
Shimoyama, K., see Fujii, K. 170 (1997) 679
Shiojima, T., see Ohkubo, M. 170 (1997) 177
Shiraki, Y., see Yaguchi, H. 170 (1997) 353
Shiraki, Y., see Pan, W. 170 (1997) 585
Shmagin, I.K., see Keller, S. 170 (1997) 349
Shukla, N., see Patrikarakos, D.G. 170 (1997) 215
Siepel, K., see Thompson, A.G. 170 (1997) 92
Silfvenius, C., B. Stålnacke and G. Landgren, MOVPE growth of strain-compensated 1300 nm $In_{1-x}Ga_xAs_yP_{1-y}$ quantum well structures 170 (1997) 122
Silvestre, L., A. Ougazzaden, D. Delprat, A. Ramdane, C. Daguet and G. Patriarche, Study of growth rate and composition variations in metalorganic vapour phase selective area epitaxy at atmospheric pressure and application to the growth of strained layer DBR lasers 170 (1997) 639
Soerensen, G., see Watkins, S.P. 170 (1997) 788
Soga, T., T. Kato, K. Baskar, C.L. Shao, T. Jimbo and M. Umeno, MOCVD growth of high-quality AlGaAs on Si substrates for high-efficiency solar cells 170 (1997) 447
Söllner, J., see Heuken, M. 170 (1997) 30
Söllner, J., see Schneider, A. 170 (1997) 767
Son, C.S., see Kim, S.-I. 170 (1997) 665
Son, M.H., see Kim, E.K. 170 (1997) 803
Sossna, E., see Kastner, M.J. 170 (1997) 188
Sotomayor-Torres, C.M., see Yates, H.M. 170 (1997) 611
Souliere, V., see Thévenot, V. 170 (1997) 251
Spika, Z., see Protzmann, H. 170 (1997) 155
Spika, Z., C. Zimprich, W. Stolz, E.O. Göbel, J. Jiang, A. Schaper and P. Werner, Correlation of ordering formation and surface structure in (GaIn)P using modulated MOVPE 170 (1997) 257
Spina, A., see Wajid, A. 170 (1997) 237
Stafford, A., S.J.C. Irvine and C.L. Griffiths, In situ measurement of the thermal and photo-assisted MOVPE of ZnTe using laser reflectometry 170 (1997) 182
Stall, R.A., see Thompson, A.G. 170 (1997) 92
Stålnacke, B., see Silfvenius, C. 170 (1997) 122
Starr, R., see Mitra, P. 170 (1997) 542
Steimetz, E., F. Schienle, J.-T. Zettler and W. Richter, Stranski–Krastanov formation of InAs quantum dots monitored during growth by reflectance anisotropy spectroscopy and spectroscopic ellipsometry 170 (1997) 208
Stenzel, O., see Dadgar, A. 170 (1997) 173
Steuber, F., see Scholz, F. 170 (1997) 321
Stillman, G.E., see Islam, M.R. 170 (1997) 413
Stoltz, S., see Peck, J. 170 (1997) 523
Stolz, W., see Protzmann, H. 170 (1997) 155
Stolz, W., see Spika, Z. 170 (1997) 257
Stolz, W., see Rettig, R. 170 (1997) 748
Strassburg, M., see Dadgar, A. 170 (1997) 173
Strauch, G., see Bergunde, T. 170 (1997) 66
Stringfellow, G.B., see Murata, H. 170 (1997) 219
Stringfellow, G.B., see Chun, Y.S. 170 (1997) 263
Strupiński, W., see Małąg, A. 170 (1997) 408
Stutzmann, M., see Ambacher, O. 170 (1997) 335
Suemune, I., T. Obinata, K. Uesugi, H. Suzuki, H. Kumano, H. Nashiki and J. Nakahara, Growth of zincblende MgS/ZnSe superlattices and their heterointerface properties 170 (1997) 480
Suruceanu, G.I., see Mawst, L.J. 170 (1997) 383
Suzuki, H., see Suemune, I. 170 (1997) 480
Suzuki, M., M. Aoki, M. Komori, H. Sato and S. Minagawa, Silicon shadow mask MOVPE for in-plane thickness control of InGaAsP/InP structures 170 (1997) 661
Syganow, V., see Scholz, F. 170 (1997) 321
Syllaios, A.J., see Bevan, M.J. 170 (1997) 467
Symons, D.M., see Booker, G.R. 170 (1997) 777
Syrbu, A.V., see Mawst, L.J. 170 (1997) 383
Sys, C., see Zhang, X. 170 (1997) 83

Tadatomo, K., see Ohuchi, Y. 170 (1997) 325
Taguchi, K., see Tsuji, M. 170 (1997) 669
Takahashi, N., see Koukitu, A. 170 (1997) 306
Takamiya, S., see Takiguchi, T. 170 (1997) 705
Takemi, M., see Takiguchi, T. 170 (1997) 705
Takemoto, A., see Takiguchi, T. 170 (1997) 705
Takemura, M., see Goto, H. 170 (1997) 510
Takeuchi, T., see Tsuji, M. 170 (1997) 669
Taki, T., see Koukitu, A. 170 (1997) 306
Takiguchi, T., T. Itagaki, M. Takemi, A. Takemoto, Y. Miyazaki, K. Shibata, Y. Hisa, K. Goto, Y. Mihashi, S. Takamiya and M. Aiga, Selective-area MOCVD growth for 1.3 μm laser diodes with a monolithically integrated waveguide lens 170 (1997) 705
Tanahashi, T., see Ekawa, M. 170 (1997) 685
Tanaka, S., S. Iwai and Y. Aoyagi, Reduction of the defect density in GaN films using ultra-thin AlN buffer layers on 6H-SiC 170 (1997) 329
Tapfer, L., see Rettig, R. 170 (1997) 748
Taudt, W., see Heuken, M. 170 (1997) 30

Taudt, W., A. Hardt, S. Lampe, H. Hamadeh and M. Heuken, Nitrogen as carrier gas for the growth of ZnSe and ZnSe:N in plasma enhanced metalorganic vapor phase epitaxy 170 (1997) 491
Taudt, W., see Gurskii, A.L. 170 (1997) 533
Taudt, W., see Prösch, G. 170 (1997) 537
Tegude, F.J., see Lindner, A. 170 (1997) 287
Te Nijenhuis, J., see Hageman, P.R. 170 (1997) 270
Theodoropoulos, C., N.K. Ingle and T.J. Mountziaris, Computational studies of the transient behavior of horizontal MOVPE reactors 170 (1997) 72
Thévenot, V., V. Souliere, H. Dumont, Y. Monteil, J. Bouix, P. Regreny and T.-M. Duc, Behaviour of vicinal InP surfaces grown by MOVPE: exploitation of AFM images 170 (1997) 251
Thomas, B., K. Ellmer, M. Müller, C. Höpfner, S. Fiechter and H. Tributsch, Structural and photoelectrical properties of $FeS_2$ (pyrite) thin films grown by MOCVD 170 (1997) 808
Thompson, A.G., R.A. Stall, W. Kroll, E. Armour, C. Beckham, P. Zawadzki, L. Aina and K. Siepel, Large scale manufacturing of compound semiconductors by MOVPE 170 (1997) 92
Thompson, J., see Wood, A.K. 170 (1997) 132
Thrush, E.J., see Zhang, X. 170 (1997) 83
Thrush, E.J., see Van der Stricht, W. 170 (1997) 344
Tischler, M.A., see Liu, J. 170 (1997) 357
Toda, A., F. Nakamura, K. Yanashima and A. Ishibashi, Blue-green laser diode grown by photo-assisted MOCVD 170 (1997) 461
Tokunaga, H., see Arai, T. 170 (1997) 88
Tran, C.A., see Arès, R. 170 (1997) 574
Tran, C.A., see Watkins, S.P. 170 (1997) 788
Triboulet, R., see Tromson-Carli, A. 170 (1997) 549
Tributsch, H., see Thomas, B. 170 (1997) 808
Trindade, T., see O'Brien, P. 170 (1997) 23
Tromson-Carli, A., A. Zozime, J. Ertel, M. Seibt, R. Druilhe, C. Grattepain and R. Triboulet, Influence of a ZnMnTe nucleation layer on the structural quality of (111) ZnTe grown by MOVPE on (100) GaAs 170 (1997) 549
Tsai, J.-H., see Liu, W.-C. 170 (1997) 438
Tsuji, M., K. Makita, T. Takeuchi and K. Taguchi, Large bandgap energy control of InAlAs/InGaAs multiple quantum wells selectively grown by low-pressure MOVPE 170 (1997) 669
Tümmler, J., J. Woitok, J. Hermans, J. Geurts, P. Schneider, D. Moulin, M. Behet and K. Heime, Growth and characterization of Sb-based heterostructures grown by LP-MOVPE 170 (1997) 772
Tuomi, T., see Hjelt, K. 170 (1997) 794
Türck, V., see Kappelt, M. 170 (1997) 590

Uekusa, S.-i., see Mizuno, Y. 170 (1997) 61
Uesugi, K., see Suemune, I. 170 (1997) 480
Umeno, M., see Soga, T. 170 (1997) 447
Underwood, R.D., see Kapolnek, D. 170 (1997) 340
Ungerechts, S., see Lakner, H. 170 (1997) 732
Uwai, K., see Kobayashi, N. 170 (1997) 225

Vaille, M., see Beaumont, B. 170 (1997) 316
Vanderbauwhede, W., X. Zhang, I. Moerman and P. Demeester, Growth and characterization of InAlGaAs(P)/InGaAs(P) MQW structures 170 (1997) 738
Van der Stricht, W., I. Moerman, P. Demeester, J.A. Crawley and E.J. Thrush, Study of GaN and InGaN films grown by metalorganic chemical vapour deposition 170 (1997) 344
Velling, P., see Lindner, A. 170 (1997) 287
Venkatasubramanian, R., T. Colpitts, E. Watko, M. Lamvik and N. El-Masry, MOCVD of $Bi_2Te_3$, $Sb_2Te_3$ and their superlattice structures for thin-film thermoelectric applications 170 (1997) 817
Verschuren, C.A., M.R. Leys, Y.S. Oei, C.G.M. Vreeburg, H. Vonk, R.T.H. Rongen and J.H. Wolter, Surface morphology of InP/InGaAs in selective area growth by chemical beam epitaxy 170 (1997) 650
Veuhoff, E., see Keidler, M. 170 (1997) 161
Vicente, P., see Booker, G.R. 170 (1997) 777
Von Eichel-Streiber, C., M. Behet, M. Heuken and K. Heime, Doping of InAs, GaSb and InPSb by low pressure MOVPE 170 (1997) 783
Vonk, H., see Verschuren, C.A. 170 (1997) 650
Vreeburg, C.G.M., see Verschuren, C.A. 170 (1997) 650

Wagner, G., see Kirpal, G. 170 (1997) 167
Wajid, A., C. Gogol, C. Hurd, M. Hetzel, A. Spina, R. Lum, M. McDonald and R.J. Capik, A high-speed high-sensitivity acoustic cell for in-line continuous monitoring of MOCVD precursor gases 170 (1997) 237
Walker, P.J., see Booker, G.R. 170 (1997) 777
Walsh, J.R., see O'Brien, P. 170 (1997) 23
Wang, B., see Chen, S. 170 (1997) 433
Wang, C.A., S. Salim, K.F. Jensen and A.C. Jones, Characteristics of GaSb growth using various gallium and antimony precursors 170 (1997) 55
Wang, C.A., Organometallic vapor phase epitaxial growth of AlSb-based alloys 170 (1997) 725
Wang, F., see Becht, M. 170 (1997) 799
Wang, Q., see Carlsson, N. 170 (1997) 127
Watkins, S.P., see Arès, R. 170 (1997) 574
Watkins, S.P., R. Arès, G. Soerensen, W. Zhong, C.A. Tran, J.E. Bryce and C.R. Bolognesi, Atomic force microscopy study of morphology and dislocation structure of InAs and GaSb grown on highly mismatched substrates 170 (1997) 788
Watko, E., see Venkatasubramanian, R. 170 (1997) 817
Watters, V.J., see Scriven, G.J. 170 (1997) 813

Weber, J., see Wiedemann, P. 170 (1997) 117
Weiler, M.H., see Mitra, P. 170 (1997) 542
Wen, J.G., see Becht, M. 170 (1997) 799
Werner, H., see Behres, A. 170 (1997) 655
Werner, P., see Spika, Z. 170 (1997) 257
Werner, P., see Heinrichsdorff, F. 170 (1997) 568
Westwater, S.P. and T.J. Bullough, The microstructure and thermal stability of CBE grown heavily carbon doped GaAs 170 (1997) 752
Weyburne, D.W. and B.S. Ahern, Design and operating considerations for a water-cooled close-spaced reactant injector in a production scale MOCVD reactor 170 (1997) 77
Weyers, M., see Bergunde, T. 170 (1997) 66
Weyers, M., see Kurpas, P. 170 (1997) 203
Weyers, M., see Knauer, A. 170 (1997) 281
Weyers, M., see Kurpas, P. 170 (1997) 442
Wickenden, A.E., W.B. Alexander, D.D. Koleske and J.A. Freitas Jr., The influence of strain and mosaic structure on electrical and optical properties of GaN films on sapphire substrates 170 (1997) 367
Wickenden, D., see Huang, Z.C. 170 (1997) 362
Wiedemann, P., G. Laube, J. Weber and E. Lach, MOVPE growth of ternary and quaternary tensile strained MQW structures for polarization insensitive devices 170 (1997) 117
Wiersch, A., see Lindner, A. 170 (1997) 287
Wilkinson, C.I., see Chen, Y.H. 170 (1997) 394
Williams, J.O., see Gnoth, D.N. 170 (1997) 198
Williams, J.O., see Fan, G.H. 170 (1997) 485
Williams, J.O., see Poole, I.B. 170 (1997) 528
Woitok, J., see Lakner, H. 170 (1997) 732
Woitok, J., see Tümmler, J. 170 (1997) 772
Wolter, J.H., see Verschuren, C.A. 170 (1997) 650
Wood, A.K., J. Thompson, N. Carr, A.J. Moseley, P.A. Bromley, M.Q. Kearley, R.W. Martin and R.J. Nicholas, Influence of substrate dopant type on the optical properties of GaInAs/InP multiquantum well structures grown by low pressure MOVPE 170 (1997) 132
Woodhead, J., see Hirotani, M. 170 (1997) 390
Woodhead, J., see Chen, Y.H. 170 (1997) 394
Woodhead, J., see Sale, T.E. 170 (1997) 399
Wright, A.C., see Gnoth, D.N. 170 (1997) 198
Wright, A.C., see Fan, G.H. 170 (1997) 485
Wright, A.C., see Poole, I.B. 170 (1997) 528
Yablonskii, G.P., see Gurskii, A.L. 170 (1997) 533
Yabuuchi, Y., see Otsuka, N. 170 (1997) 626
Yaguchi, H., S. Miyoshi, G. Biwa, M. Kibune, K. Onabe, Y. Shiraki and R. Ito, Photoluminescence excitation spectroscopy of $GaP_{1-x}N_x$ alloys: conduction-band-edge formation by nitrogen incorporation 170 (1997) 353
Yaguchi, H., see Pan, W. 170 (1997) 585
Yakovlev, V.P., see Mawst, L.J. 170 (1997) 383
Yamaguchi, M., see Kudo, K. 170 (1997) 634
Yamaguchi, T., see Ohkubo, M. 170 (1997) 177
Yamauchi, A., see Fujii, K. 170 (1997) 679
Yanashima, K., see Toda, A. 170 (1997) 461
Yates, H.M., W.R. Flavell, M.E. Pemble, N.P. Johnson, S.G. Romanov and C.M. Sotomayor-Torres, Novel quantum confined structures via atmospheric pressure MOCVD growth in asbestos and opals 170 (1997) 611
Yom, S.S., see Kim, E.K. 170 (1997) 803
Yoshida, H., see Kamata, A. 170 (1997) 518
Zahn, D.R.T., see Prösch, G. 170 (1997) 537
Zahn, D.R.T., see Schneider, A. 170 (1997) 767
Zanotti Fregonara, C., see Mazzer, M. 170 (1997) 553
Zawadzki, P., see Thompson, A.G. 170 (1997) 92
Zettler, J.-T., see Steimetz, E. 170 (1997) 208
Zhang, X., I. Moerman, C. Sys, P. Demeester, J.A. Crawley and E.J. Thrush, Highly uniform AlGaAs/GaAs and InGaAs(P)/InP structures grown in a multiwafer vertical rotating susceptor MOVPE reactor 170 (1997) 83
Zhang, X., see Vanderbauwhede, W. 170 (1997) 738
Zhang, X.G., see Bao, K.X. 170 (1997) 497
Zhao, G., see Bao, K.X. 170 (1997) 497
Zhi, D., see Liu, J. 170 (1997) 357
Zhong, W., see Watkins, S.P. 170 (1997) 788
Zimmermann, G., A. Ougazzaden, A. Gloukhian, E.V.K. Rao, D. Delprat, A. Ramdane and A. Mircea, Selective area MOVPE growth of InP, InGaAs and InGaAsP using TBAs and TBP at different growth conditions 170 (1997) 645
Zimprich, C., see Spika, Z. 170 (1997) 257
Zorn, M., see Knorr, K. 170 (1997) 230
Zozime, A., see Tromson-Carli, A. 170 (1997) 549

ELSEVIER

Journal of Crystal Growth 170 (1997) 834–836

JOURNAL OF CRYSTAL GROWTH

# Subject index

Apparatus
– for chemical beam epitaxy
– – of multiwafers 16
– for production scale metalorganic chemical vapor deposition reactor 77
– for thin film growth by a rotating susceptor 83

Characterization
– by atomic force microscopy
– – of III–V compounds 357, 566, 788
– by deep level transient spectroscopy
– – of II–VI compounds 537
– by photoluminescence
– – of III–V compounds 372
– by Raman scattering
– – of II–VI compounds 767
– by thermally stimulated currents
– – of III–V compounds 362
– by X-ray diffusion
– – of III–V compounds 47, 357
Computer simulation
– of heat transfer in metalorganic chemical vapor deposition 66
– of transient behaviour of horizontal metalorganic vapor phase epitaxy 72
Crystalline form, special
– nanostructure 476
– quantum dots 568, 700

Device characterization
– caustic cell 237
– diodes 503
– electron field emission 340
– electronic materials 92, 103, 173, 287, 725, 803
– heterojunction 30, 177, 263, 329, 377, 383,408, 413, 424, 442, 574, 595, 725, 732
– lasers 11, 109, 161, 281, 377, 383, 394, 399, 404, 408, 418, 456, 585, 621, 639, 705, 715, 719, 725
– quantum wells 30, 117, 122, 127, 132, 281, 349, 377, 383, 390, 399, 408, 456, 595, 611, 621, 626, 634, 639, 669, 695, 732, 738, 748
– quantum wires 585, 590, 595, 605
– solar cells 447
– transistors 428, 433, 451, 456
Diffusional control
– of lithium nitrate in zinc selenide 503
Diodes, see Device characterization

Doping in
– gallium arsenide 270, 292, 297, 372, 752
– indium phosphide 685
– zinc selenide 472, 491, 533

Electronic materials, see Device characterization
Etching
– chemical 616, 674

Gallium
– aluminum arsenide 88
– antimonide 1, 55
– arsenide 83
– indium arsenide 83, 88

Heterojunction, see Device characterization

Indium
– gallium nitride 11
– phosphide 77

Kinetics
– of diffusion 177
– of growth 39, 61, 149, 161, 182, 188, 208, 219, 276, 590, 650, 655, 689
– of in situ formation of nanostructures 39
– of interface control 188, 281, 689
– of nucleation 39, 193, 208, 246, 558

Lasers, see Device characterization
Lasers, crystals for
– blue emission 30

Morphological stability
– of gallium nitride tips 335
– of indium phosphide/indium gallium arsenide 650

Nucleation
– of cadmium telluride, theory 193
– of indium arsenide on gallium arsenide 208
– of indium gallium arsenide 568
– of Stranski–Krastanov islands 39
Numbers
– Peclet 72

Precursor
– for aluminum gallium indium phosphide 97
– for aluminum nitride 139, 335
– for arsenic 149
– for carbon 665
– for dopants 173
– for gallium antimonide 55
– for gallium indium arsenide 167
– for gallium indium arsenide phosphate 97, 167
– for gallium indium phosphide 97
– for gallium nitride 139, 325, 335
– for indium nitride 139
– for indium phosphide 97
– for phosphor 149
– for zinc manganese sulphide selenide 30

Quantum wells, see Device characterization
Quantum wires, see Device characterization

Solar cells, see Device characterization
Superconductivity materials, high $T_c$
– film
– – of YBCO 242
Superlattices, multilayers
– of III–V compounds 621, 665, 732, 748
– of II–VI compounds 480
Surface morphology
– of aluminum nitride 329
– of gallium nitride 312, 316, 329
– of indium gallium arsenide 566
Surface structure
– of gallium arsenide 127, 225
– of gallium indium phosphide 127, 225, 257
– of gallium phosphide 225
– of indium arsenide 225
– of indium gallium arsenide 225
– of indium phosphide 225
– of rutile 803
– of III–V surfaces 230

Thin film growth, epitaxy
– by atomic layer epitaxy
– – of gallium arsenide 574
– – of indium arsenide 574
– – of indium phosphide 215
– by chemical beam epitaxy
– – of gallium arsenide 752
– – of indium gallium arsenide 650
– – of indium gallium phosphide 16
– – of indium phosphide 16, 650
– by metalorganic molecular beam epitaxy
– – of gallium aluminum arsenide 674
– – of gallium arsenide 297, 674
– – of gallium indium arsenide 161, 456
– – of gallium indium phosphide 161
– – of indium gallium arsenide 177, 287
– – of indium phosphide 161
– – theory of thermodynamics 306
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of cadmium sulphide 23
– – – of lead sulphide 23
– – – theory of flow fields in epitaxial growth 61
– – through metalorganic chemical vapor deposition
– – – of aluminum antimonide 772
– – – of aluminum arsenide 246, 404, 719
– – – of aluminum gallium antimonide 725
– – – of aluminum gallium arsenide 83, 88, 92, 390, 394, 404, 408, 447, 585, 600, 605, 621, 665, 679, 689, 700, 757
– – – of aluminum gallium arsenide antimonide 725
– – – of aluminum nitride 139, 329, 335
– – – of antimony telluride 187
– – – of bismuth telluride 187
– – – of cadmium sulphide 23, 528
– – – of cadmium telluride 193, 553
– – – of cadmium zinc selenide 497
– – – of cerium oxide 799
– – – of gallium antimonide 55, 777, 783, 788, 794
– – – of gallium arsenide 1, 39, 83, 88, 92, 97, 127, 203, 246, 270, 292, 372, 377, 390, 408, 424, 428, 433, 438, 442, 574, 579, 600, 605, 665, 689, 700, 719, 762, 772
– – – of gallium arsenide phosphide 585, 748
– – – of gallium indium arsenide 88, 103, 155
– – – of gallium indium arsenide phosphide 97
– – – of gallium indium nitride 321, 344, 349
– – – of gallium indium phosphide 88, 97, 127, 203, 219
– – – of gallium nitride 11, 139, 312, 316, 321, 325, 329, 335, 340, 344, 367
– – – of gallium phosphide nitride 353
– – – of germanium 1
– – – of indium aluminum arsenide 590, 595, 669
– – – of indium arsenide 203, 558, 574, 772, 783, 788
– – – of indium arsenide phosphide 122, 616
– – – of indium gallium aluminum arsenide 399, 738
– – – of indium gallium aluminum phosphide 92, 103, 394, 399, 418, 595
– – – of indium gallium arsenide 83, 92, 117, 127, 132, 167, 377, 390, 394, 438, 451, 568, 579, 590, 616, 639, 645, 661, 669, 695, 700, 705, 743, 748
– – – of indium gallium arsenide phosphide 109, 113, 117, 122, 167, 237, 281, 383, 626, 634, 645, 661, 732, 738, 757
– – – of indium gallium phosphide 39, 122, 257, 263, 377, 383, 413, 428, 442, 710
– – – of indium nitride 139, 301
– – – of indium phosphide 39, 83, 92, 97, 103, 109, 113, 127, 132, 173, 215, 251, 301, 424, 433, 451, 590, 611, 626, 639, 645, 655, 661, 685, 695, 715
– – – of indium phosphide antimonide 772, 783
– – – of iron sulphide 808
– – – of lead sulphide 23
– – – of magnesium sulphide 480, 528
– – – of mercury cadmium telluride 542
– – – of rutile 803
– – – of yttrium barium cuprates 224
– – – of zinc arsenide 813
– – – of zinc cadmium selenide 461

– – – of zinc iron selenide 523
– – – of zinc magnesium sulphide selenide 30, 461
– – – of zinc manganese telluride 549
– – – of zinc selenide 144, 188, 461, 467, 472, 480, 485, 491, 503, 507, 510, 518, 533, 537
– – – of zinc selenide telluride 514, 518
– – – of zinc sulphide 476
– – – of zinc sulphide selenide 461, 767
– – – of zinc telluride 549
– – – theory of convection 72
– – – theory of gas flow 77
– – – theory of heat transfer 66
– – – theory of thermal decomposition 485
Transistors, see Device characterization